### Step 1: Substrate Stack



- · Width: 5000 nm
- · 5000 nm
- · Layer 1: Silicon
- · Thickness: 1000 nm
- · Layer 2: Gunk
- · Thickness: 100 nm

Silicon

Gunk

MMA EL13

PMMA A6

Aluminium

Comments: 111 crystal axix

### Step 2: 3 Solvent Clean



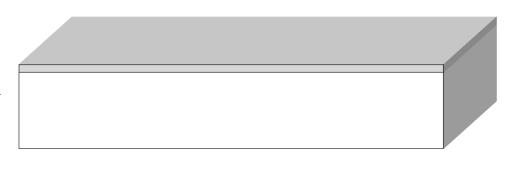
Beakers + Sonicator

- · Chemical: Acetone
- Time: 5 mins
- **Temp:** 20 °C
- · Ultra Sonic: true

**Comments:** Sonicate in Acetone for 6 minutes

Sonicate in Methanol for 3 minutes

Sonicate in IPA for 3 minutes



Silicon

Gunk

MMA EL13

PMMA A6

Aluminium

### Step 3: DI Water Rinse



Beakers

· Chemical: DI Water

• Time: 30 secs

• **Temp:** 25 °C

· Ultra Sonic: false

Silicon

Gunk

MMA EL13

PMMA A6

Aluminium

**Comments:** Dry with N2 gun

### Step 4: Dehydration Bake



Bake Plate

• **Temp:** 110 °C

· Time: 20 secs

Silicon

Gunk

MMA EL13

PMMA A6

Aluminium

**Comments:** 110 to 180 degree C allowed

### Step 5: Spin Resist



### Spinner

- · Material: MMA EL13
- · Thickness: 620 nm
- · **Spin Speed:** 3000 rpm
- **Spin Time:** 60 secs

Silicon
Gunk
MMA EL13
PMMA A6
Aluminium

**Comments:** 

### Step 6: Softbake

Fabublex
Your Friendly Fab Assistant

Bake Plate

• **Temp:** 180 °C

• **Time:** 300 secs

Silicon
Gunk
MMA EL13
PMMA A6
Aluminium

Comments:

### Step 7: Spin Resist



### Spinner

- · Material: PMMA A6
- · Thickness: 300 nm
- · **Spin Speed:** 4000 rpm
- **Spin Time:** 60 secs

Silicon
Gunk
MMA EL13
PMMA A6
Aluminium

Comments:

### Step 8: Softbake



Bake Plate

• **Temp:** 180 °C

• **Time:** 300 secs

Silicon
Gunk
MMA EL13
PMMA A6
Aluminium

**Comments:** 

# Step 9: Electron-Beam Lithography



Raith EBPG 5150

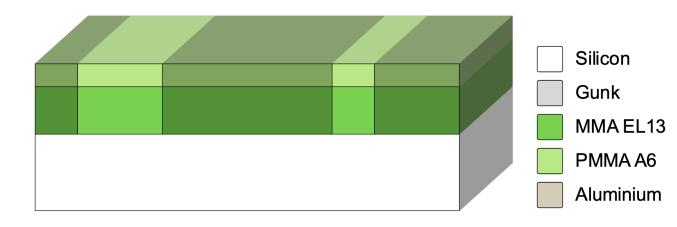
Voltage: 100 kV

· Current: 100 nA

• **Dose:** 290 μC/cm<sup>2</sup>

• **Dwell Time:** <none> ns

**Comments:** 



### Step 10: Develop



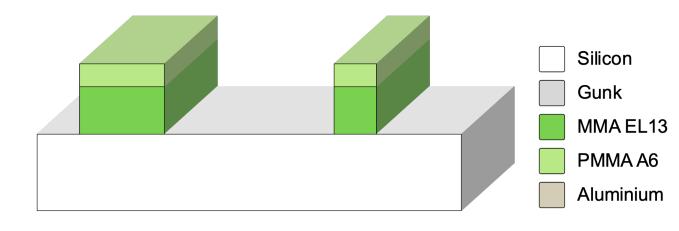
#### Beaker

· **Developer:** MIBK:IPA

· Time: 180 secs

Temp: 20 °C

Comments: MIBK:IPA = 1:1



### Step 11: Pre-Ash

# Fabubles Your Friendly Fab Assistant

#### YES 02 Plasma

· Material: Gunk

• **Depth:** 0 nm

· Gasses: Oxygen

• Etch Rate: <none> nm/s

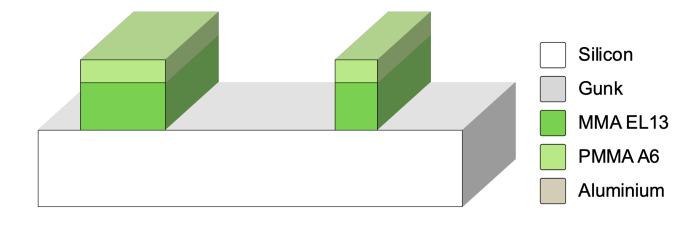
• Time: 30 secs

· RF Power: 60 Watts

• **Pressure:** 0.3 Torr

•

Comments:



### Step 12: E-beam Evaporation



#### Angstrom

· Material: Aluminium

· Thickness: 1000 Å

• Deposition Rate: 4 Å/s

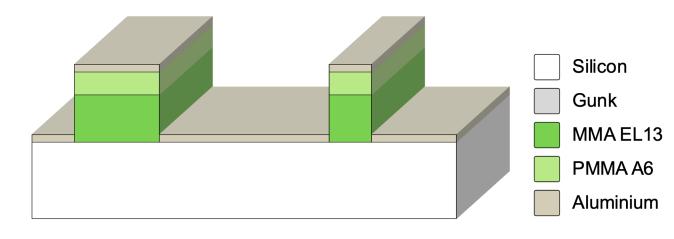
• Beam Current: <none> Amps

Beam Voltage: <none> kV

· Pressure: <none> Torr

Deposition Angle: 0°

**Comments:** 



# Step 13: Lift-Off

Fab<sub>µ</sub>Blox

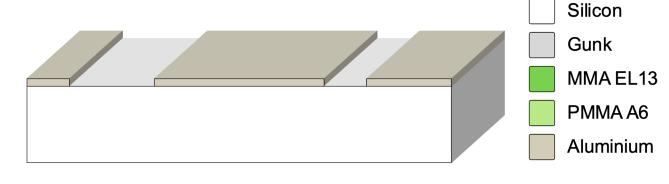
Beaker + Sonicator

· Solvent: Acetone

• Time: 3 hours

• **Temp:** 45 °C

**Comments:** 



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LIFTOFF

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### Step 14: 3 Solvent Clean



#### Beaker

· Chemical: Acetone

• Time: 30 secs

Temp: 25 °C

· Ultra Sonic: true

**Comments:** Sonicate the chip in the acetone liftoff beaker for 30 seconds (more time if the liftoff has not been completed.)

With the acetone wash bottle in the CUSTO PROPER ARIND, take the chip out of the

acotono clowly ac maintaining a

Silicon

Gunk

MMA EL13

PMMA A6

Aluminium

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### Step 15: DI Water Rinse



#### Beaker

· Chemical: DI Water

• Time: 30 secs

• **Temp:** 25 °C

· Ultra Sonic: false

Gunk

MMA EL13

PMMA A6

Aluminium

**Comments:** Dry with N2 gun

Section: Dissipator Device Recipe

Silicon